CLAIMS

1. A sputtering target member for a magnetic recording layer, comprising 10 to 70 mol% of Co, 5 to 30 mol% of Pt, 1.5 to 10 mol% of carbide, and a total of 0 to 30 mol% of one or more non-magnetic materials selected from carbon, oxides, nitrides, and carbonitrides, wherein a molar ratio of the carbide to a total of the carbon and the carbide is 0.25 or more.

2. The sputtering target member for a magnetic recording layer according to claim 1, wherein a molar ratio of the carbide to a total of the carbon and the carbide is 0.4 or more.

3. The sputtering target member for a magnetic recording layer according to claim 1 or 2, wherein the carbide comprises one or more selected from B_4C, Cr_3C_2, and TiC.

4. The sputtering target member for a magnetic recording layer according to claim 3, comprising a total of 1.5 to 10 mol% of one or more selected from B_4C, Cr_3C_2, and TiC.

5. The sputtering target for a magnetic recording layer according to any one of claims 1 to 4, comprising a total of 30 mol% or less of one or more metal elements selected from Cr, Ru, B, Ti, Si, and Mn.

6. The sputtering target member for a magnetic recording layer according to any one of claims 1 to 5, wherein a relative density is 90% or more.

7. A sputtering target assembly, comprising the sputtering target member for a magnetic recording layer according to any one of claims 1 to 6, and a backing tube or a backing plate bonded to the sputtering target member.

8. A method for forming a film, comprising sputtering the sputtering target member for a magnetic recording layer according to any one of claims 1 to 6.